Since of £1, B can be large! so ic>>le -> amplification Why large gain? B~1 whereas is and ic controlled by

and ic controlled by

and ic controlled by

is determines ic from lifetimes T and charge neutrality. Transittime of hole from emitter to collector = T+ Hole lifetime in base = Tp average excess hole spends in base average excess electron spends Tp in base (assuming regligible e-injection into emitter, 8=1) so base stays neutral But

now put real numbers for Tp and Tt into BJT circuit: T = 0.1 MS Can get Tt << Tp by design: (Recall Lp= VD-Tp recombination low in base  $\frac{3500 \Omega}{50 \text{ is}} = \frac{5 \text{ V}}{50 \text{ K} \Omega} = 0.1 \text{ mA}$ biased VBE) CB reverse-biased 4 Nc= 10 mA

Common-emitter circuit: E common to both base and collector circuits

ic determined by B and LB,
not by collector circuit Rand V

. If prop were a short ic = 10V =

. If prop were a short, ic =  $\frac{10V}{500 - 2} = 20 \text{ mA}$ ;
but 5V across reverse-biased BC junction
so  $10-5 = \frac{5V}{500 - 2} = 10 \text{ mA}$ 

If is had an a-c component, ic would too, but amplified by 100.

Gain comes from small base current forcing EB junction to inject large hole current (Since Tp>>Te)

Calculation of minority carrier distributions and terminal currents

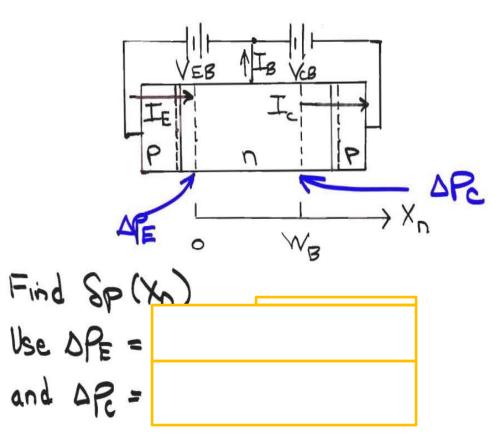
Step 1) Find excess hole distribution in base

step 2) Find IEP and I from gradient of hole distribution

Step 3) Find IB from Kirchoff's Law

- Simplifying assumptions:

  a) Neglect drift only diffusion in base
- b) Neglect electron emission oument: 8=1
  (all holes)
- c) Neglect collector saturation current
- d) Uniform cross section A: 1-D flow
- e) All currents and voltages steady state



If emitter strongly forward-biased,

VEB >> KT/g

If collector strongly reverse-biased,

VCB LLO

Then DP= = (equilibrium courrier

OPC = concentration depleted)

Solve diffusion equation S&B Eqs. 4-34
$$\frac{d^2 SP(X_n)}{dX^2} = \frac{SP(X_n)}{L_p^2}$$

Again, general solution is: Sp(Xn) = C, e Xn/Lp+Cze-Xn/Lp

Lp =

Now boundary conditions can't eliminate a constant since Sp(Xn) doesn't go to zero for large Xn.

In fact, Who short versus Lp

-> most carriers reach collector

-> Xn/Lp is small.

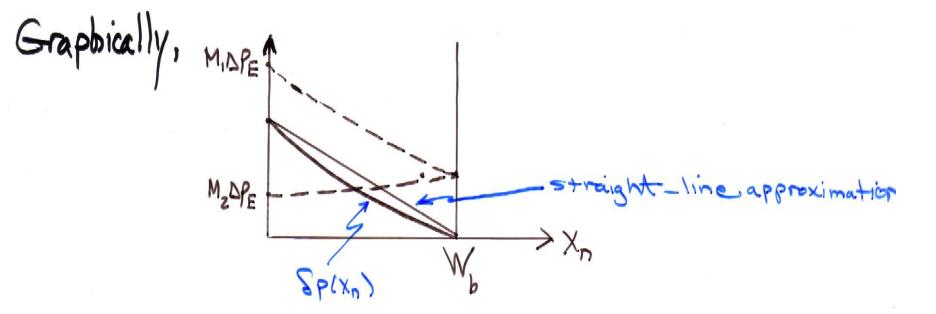
For strong reverse bias, DP=-Pr and assume DP=0 compared to DP=

Then 
$$C_1 = -\Delta P_E e^{-W_b/Lp}$$
 and  $C_2 = \frac{\Delta P_E e^{W_b/Lp}}{(e^{W_b/Lp} - e^{-W_b/Lp})}$ 

So  $S_P(X_D) = \Delta P_E = \frac{(e^{(W_b - X_D)/Lp} - e^{-(W_b - X_D)/Lp})}{e^{W_b/Lp} - e^{-(W_b - X_D)/Lp}}$ 

(for  $\Delta P_C = 0$ )

Put C, and Cz into Sp(xn) = C, exn/Lp+Cze-xn/Lp one simplified (but very useful) solution: strongly reversed biased collector (
and DPE DPC LDPC) Then C, and Cz simplify and SP(Xn) = M, DPE e-Xn/Lp = M, DPE e-Xn/Lp = Mz DPE e where M, = e Wb/LP



will see deviation from linearity due to base recombination.

We've got Sp(xn) now.

Step 2. Find emitter and collector currents

Eg. 4-22 b for holes

Use C. and Cz to make calculation easier.

Substitute later.

Now substitute C. and Cz back in.

(see next-page for details)

Tp (Xn=0) = Tep = gADp (APE ctnh Wb-AP (Sch Wb)

Lp (Xn=Wb) = Tc = gADp (APE csch Wb - AP ctnh Wb)

Tp (Xn=Wb) = Tc = gADp (APE csch Wb - AP ctnh Wb)

Lp

Now get IB from I Epand Ic = Step 3

Now get IB from IEP and Icp: Step3

IB = IE - Ic

IB = BADP [(DPE + DPe) tanh Wb ]

IB = BADP [(DPE + DPe) tanh ZLp)]

see next page for details

$$T_{B} = T_{E} - T_{c}$$

$$= \frac{1}{2} \frac{1}{2} \left[ \frac{1}{2} \left( \frac{1}{2} \frac{1}{2} \right) - \frac{1}{2} \left( \frac{1}{2} \frac{1}{2} \right) \right]$$

$$T_{B} = \frac{1}{2} \frac{1}{2} \frac{1}{2} \left[ \frac{1}{2} \left( \frac{1}{2} \frac{1}{2} \frac{1}{2} \right) \left( \frac{1}{2} \frac{1}{2} \frac{1}{2} \frac{1}{2} \right) \left( \frac{1}{2} \frac{1}{2} \frac{1}{2} \frac{1}{2} \frac{1}{2} \right) \right]$$

$$T_{B} = \frac{1}{2} \frac{1}{2} \frac{1}{2} \left[ \frac{1}{2} \frac{1}{2}$$